

NBA3N200S

3.3 V Automotive Grade M-LVDS Driver Receiver

Description

The NBA3N200S is a 3.3 V supply differential Multipoint Low Voltage (M-LVDS) line Driver and Receiver for automotive applications. NBA3N200S offers the Type-1 receiver threshold at 0.0 V.

The NBA3N200S has Type-1 receivers that detect the bus state with as little as 50 mV of differential input voltage over a common-mode voltage range of -1 V to 3.4 V. Type-1 receivers have near zero thresholds (± 50 mV) and exhibit 25 mV of differential input voltage hysteresis to prevent output oscillations with slowly changing signals or loss of input.

NBA3N200S supports Simplex or Half Duplex bus configurations.

Features

- Low-Voltage Differential 30 Ω to 55 Ω Line Drivers and Receivers for Signaling Rates Up to 200 Mbps
- Type-1 Receivers Incorporate 25 mV of Hysteresis
- Controlled Driver Output Voltage Transition Times for Improved Signal Quality
- -1 V to 3.4 V Common-Mode Voltage Range Allows Data Transfer With up to 2 V of Ground Noise
- Bus Pins High Impedance When Disabled or $V_{CC} \leq 1.5$ V
- M-LVDS Bus Power Up/Down Glitch Free
- Operating range: $V_{CC} = 3.3 \pm 10\%$ V (3.0 to 3.6 V)
- Operation from -40°C to 125°C
- AEC-Q100 Qualified and PPAP Capable
- These are Pb-Free Devices

Applications

- Low-Power High-Speed Short-Reach Alternative to TIA/EIA-485
- Backplane or Cabled Multipoint Data and Clock Transmission
- Cellular Base Stations
- Central-Office Switches
- Network Switches and Routers
- Automotive



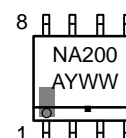
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**SOIC-8
D SUFFIX
CASE 751**

MARKING DIAGRAMS



NA200 = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
■ = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information on page 18 of this data sheet.

NBA3N200S

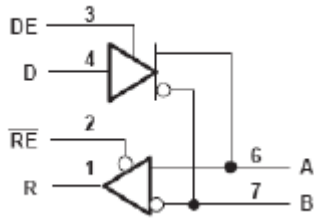


Figure 1. Logic Diagram

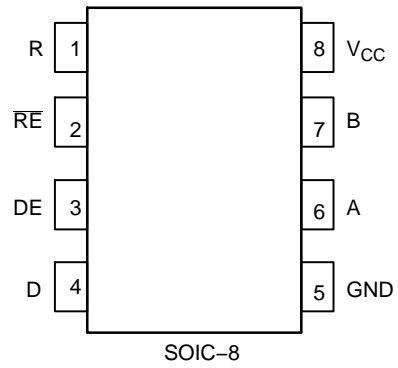


Figure 2. Pinout Diagram
(Top View)

Table 1. PIN DESCRIPTION

Number	Name	I/O Type	Open Default	Description
1	R	LVC MOS Output		Receiver Output Pin
2	RE	LVC MOS Input	High	Receiver Enable Input Pin (LOW = Active, HIGH = High Z Output)
3	DE	LVC MOS Input	Low	Driver Enable Input Pin (LOW = High Z Output, HIGH=Active)
4	D	LVC MOS Input		Driver Input Pin
5	GND			Ground Supply pin. Pin must be connected to power supply to guarantee proper operation.
6	A	M-LVDS Input /Output		Transceiver True Input/Output Pin
7	B	M-LVDS Input /Output		Transceiver Invert Input/Output Pin
8	VCC			Power Supply pin. Pin must be connected to power supply to guarantee proper operation.

NBA3N200S

Table 2. DEVICE FUNCTION TABLE

TYPE 1 Receiver	Inputs		Output	
	$V_{ID} = V_A - V_B$	\overline{RE}	R	
	$V_{ID} \geq 50 \text{ mV}$	L	H	
	$-50 \text{ mV} < V_{ID} < 50 \text{ mV}$	L	?	
	$V_{ID} \leq -50 \text{ mV}$	L	L	
	X	H	Z	
	X	Open	Z	
	Open	L	?	
	Open	H	Z	
DRIVER	Input	Enable	Output	
	D	DE	A / Y	B / Z
	L	H	L	H
	H	H	H	L
	Open	H	L	H
	X	Open	Z	Z
	X	L	Z	Z
	X	H	Z	Z

H = High, L = Low, Z = High Impedance, X = Don't Care, ? = Indeterminate

NBA3N200S

Table 3. ATTRIBUTES (Note 1)

Characteristics			Value
ESD Protection	Human Body Model (JEDEC Standard 22, Method A114–A)	A, B All Pins	±6 kV ±2 kV
	Machine Model	All Pins	±200 V
	Charged –Device Model (JEDEC Standard 22, Method C101)	All Pins	±1500 V
Moisture Sensitivity, Indefinite Time Out of Drypack (Note 1)			Level 1
Flammability Rating Oxygen Index			UL–94 code V–0 A 1/8" 28 to 34
Transistor Count			917 Devices
Meets or exceeds JEDEC Spec EIA/JESD78 IC Latchup Test			

1. For additional information, see Application Note AND8003/D.

Table 4. MAXIMUM RATINGS (Note 2)

Symbol	Parameter	Condition 1	Condition 2	Rating	Unit
V _{CC}	Supply Voltage			–0.5 ≤ V _{CC} ≤ 4.0	V
V _{IN}	Input Voltage	D, DE, RE		–0.5 ≤ V _{IN} ≤ 4.0	V
		A, B		–1.8 ≤ V _{IN} ≤ 4.0	
I _{OUT}	Output Voltage	R A, B		–0.3 ≤ I _{OUT} ≤ 4.0 –1.8 ≤ I _{OUT} ≤ 4.0	V
T _A	Operating Temperature Range, Industrial			–40 to ≤ +125	°C
T _{stg}	Storage Temperature Range			–65 to +150	°C
θ _{JA}	Thermal Resistance (Junction–to–Ambient)	0 lfpm 500 lfpm	SOIC–8	190 130	°C/W °C/W
θ _{JC}	Thermal Resistance (Junction–to–Case)	(Note 3)	SOIC–8	41 to 44	°C/W
T _{sol}	Wave Solder			265	°C
P _D	Power Dissipation (Continuous)		T _A = 25°C 25°C < T _A < 125°C T _A = 125°C	725 5.8 377	mW mW/°C mW

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

2. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and not valid simultaneously.

If stress limits are exceeded device functional operation is not implied, damage may occur and reliability may be affected.

3. JEDEC standard multilayer board – 2S2P (2 signal, 2 power).

NBA3N200S

Table 5. DC CHARACTERISTICS VCC = 3.3 ±10% V(3.0 to 3.6 V), GND = 0 V, TA = -40°C to +125°C (See Notes 4, 5)

Symbol	Characteristic	Min	Typ	Max	Unit
ICC	Power Supply Current Receiver Disabled Driver Enabled RE and DE at VCC, RL = 50 Ω, All others open Driver and Receiver Disabled RE at VCC, DE at 0 V, RL = No Load, All others open Driver and Receiver Enabled RE at 0 V, DE at VCC, RL = 50 Ω, All others open Receiver Enabled Driver Disabled RE at 0 V, DE at 0 V, RL = 50 Ω, All others open		13 1 16	22 4 24 13	mA
VIH	Input HIGH Voltage	2		VCC	V
VIL	Input LOW Voltage	GND		0.8	V
VBUS	Voltage at any bus terminal VA, VB, VY or VZ	-1.4		3.8	V
VID	Magnitude of differential input voltage	0.05		VCC	

DRIVER

VAB	Differential output voltage magnitude (see Figure 4)	440		690	mV
Δ VAB	Change in Differential output voltage magnitude between logic states (see Figure 4)	-50		50	mV
VOS(SS)	Steady state common mode output voltage (see Figure 5)	0.8		1.2	V
ΔVOS(SS)	Change in Steady state common mode output voltage between logic states (see Figure 5)	-50		50	mV
VOS(PP)	Peak-to-peak common-mode output voltage (see Figure 5)			150	mV
VAOC	Maximum steady-state open-circuit output voltage (see Figure 9)	0		2.4	V
VBOC	Maximum steady-state open-circuit output voltage (see Figure 9)	0		2.4	V
VP(H)	Voltage overshoot, low-to-high level output (see Figure 7)			1.2 VSS	V
VP(L)	Voltage overshoot, high-to-low level output (see Figure 7)	-0.2 VSS			V
I _{IH}	High-level input current (D, DE) VIH = 2 V	0		10	uA
I _{IL}	Low-level input current (D, DE) VIL = 0.8 V	0		10	uA
JI _{OSJ}	Differential short-circuit output current magnitude (see Figure 6)			24	mA
I _{OZ}	High-impedance state output current (driver only) -1.4 V ≤ (VA or VB) ≤ 3.8 V, other output at 1.2 V	-15		10	uA
I _{O(OFF)}	Power-off output current (0 V ≤ VCC ≤ 1.5 V) -1.4 V ≤ (VA or VB) ≤ 3.8 V, other output at 1.2 V	-10		10	uA

RECEIVER

V _{IT+}	Positive-going Differential Input voltage Threshold (See Figure 11 & Table 8) Type 1			50	mV
V _{IT-}	Negative-going Differential Input voltage Threshold (See Figure 11 & Table 8) Type 1	-50			mV
V _{HYS}	Differential Input Voltage Hysteresis (See Figure 11 and Table 2) Type 1		25		mV
VOH	High-level output voltage (IOH = -8 mA)	2.4			V
VOL	Low-level output voltage (IOL = 8 mA)			0.4	V
I _{IH}	RE High-level input current (VIH = 2 V)	-10		0	μA
I _{IL}	RE Low-level input current (VIL = 0.8 V)	-10		0	μA
I _{OZ}	High-impedance state output current (VO = 0 V of 3.6 V)	-10		15	μA
CA / CB	Input Capacitance VI = 0.4 sin(30E ⁶ πt) + 0.5 V, other outputs at 1.2 V using HP4194A impedance analyzer (or equivalent)		3		pF
C _{AB}	Differential Input Capacitance VAB = 0.4 sin(30E ⁶ πt) V, other outputs at 1.2 V using HP4194A impedance analyzer (or equivalent)			2.5	pF
CA/B	Input Capacitance Balance, (CA/CB)	99		101	%

NBA3N200S

Table 5. DC CHARACTERISTICS VCC = 3.3 ±10% V(3.0 to 3.6 V), GND = 0 V, TA = -40°C to +125°C (See Notes 4, 5)

Symbol	Characteristic	Min	Typ (Note 5)	Max	Unit
BUS INPUT AND OUTPUT					
IA	Input Current Receiver or Transceiver with Driver Disabled VA = 3.8 V, VB = 1.2 V VA = 0.0 V or 2.4 V, VB = 1.2 V VA = -1.4 V, VB = 1.2 V	0 -20 -32		32 20 0	uA
IB	Input Current Receiver or Transceiver with Driver Disabled VB = 3.8 V, VA = 1.2 V VB = 0.0 V or 2.4 V, VA = 1.2 V VB = -1.4 V, VA = 1.2 V	0 -20 -32		32 20 0	uA
IAB	Differential Input Current Receiver or Transceiver with driver disabled (IA-IB) VA = VB, -1.4 ≤ VA ≤ 3.8 V	-4		4	uA
IA(OFF)	Input Current Receiver or Transceiver Power Off 0V ≤ VCC ≤ 1.5 and: VA = 3.8 V, VB = 1.2 V VA = 0.0 V or 2.4 V, VB = 1.2 V VA = -1.4 V, VB = 1.2 V	0 -20 -32		32 20 0	uA
IB(OFF)	Input Current Receiver or Transceiver Power Off 0V ≤ VCC ≤ 1.5 and: VB = 3.8 V, VA = 1.2 V VB = 0.0 V or 2.4 V, VA = 1.2 V VB = -1.4 V, VA = 1.2 V	0 -20 -32		32 20 0	uA
IAB(OFF)	Receiver Input or Transceiver Input/Output Power Off Differential Input Current; (IA-IB) VA = VB, 0 ≤ VCC ≤ 1.5 V, -1.4 ≤ VA ≤ 3.8 V	-4		4	uA
CA	Transceiver Input Capacitance with Driver Disabled VA = 0.4 sin(30E6πt) + 0.5 V using HP4194A impedance analyzer (or equivalent); VB = 1.2 V		5		pF
CB	Transceiver Input Capacitance with Driver Disabled VB = 0.4 sin(30E6πt) + 0.5 V using HP4194A impedance analyzer (or equivalent); VA = 1.2 V		5		pF
CAB	Transceiver Differential Input Capacitance with Driver Disabled VA = 0.4 sin(30E6πt) + 0.5 V using HP4194A impedance analyzer (or equivalent); VB = 1.2 V			3.0	pF
CA/B	Transceiver Input Capacitance Balance with Driver Disabled, (CA/CB)	99		101	%

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

4. See Figure 3. DC Measurements reference.

5. Typ value at 25°C and 3.3 VCC supply voltage.

Table 6. DRIVER AC CHARACTERISTICS VCC = 3.3 ±10% V(3.0 to 3.6 V), GND = 0 V, TA = -40°C to +125°C (Note 6)

Symbol	Characteristic	Min	Typ	Max	Unit
tPLH / tPHL	Propagation Delay (See Figure 7)	1.0	1.5	2.4	ns
tPHZ / tPLZ	Disable Time HIGH or LOW state to High Impedance (See Figure 8)			7	ns
tPZH / tPZL	Enable Time High Impedance to HIGH or LOW state (See Figure 8)			7	ns
tSK(P)	Pulse Skew (tPLH - tPHL) (See Figure 7)		0	150	ps
tSK(PP)	Device to Device Skew similar path and conditions (See Figure 7)			1	ns
tJIT(PER)	Period Jitter RMS, 100 MHz (Source tr/ff 0.5 ns, 10 and 90% points, 30k samples. Source jitter de-embedded from Output values) (See Figure 10)		2	3.5	ps
tJIT(PP)	Peak-to-peak Jitter, 200 Mbps 2 ¹⁵ -1 PRBS (Source tr/ff 0.5 ns, 10 and 90% points, 100k samples. Source jitter de-embedded from Output values) (See Figure 10)		30	160	ps
tr / tf	Differential Output rise and fall times (See Figure 7)	0.9		1.6	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

6. Typ value at 25°C and 3.3 VCC supply voltage.

NBA3N200S

Table 7. RECEIVER AC CHARACTERISTICS $V_{CC} = 3.3 \pm 10\% V$ (3.0 to 3.6 V), $GND = 0 V$, $T_A = -40^\circ C$ to $+125^\circ C$ (Note 7)

Symbol	Characteristic	Min	Typ	Max	Unit
t_{PLH} / t_{PHL}	Propagation Delay (See Figure 12)	2	4	6	ns
t_{PHZ} / t_{PLZ}	Disable Time HIGH or LOW state to High Impedance (See Figure 13)			10	ns
t_{PZH} / t_{PZL}	Enable Time High Impedance to HIGH or LOW state (See Figure 13)			18	ns
$t_{SK(P)}$	Pulse Skew ($ t_{PLH} - t_{PHL} $) (See Figure 14) $C_L = 5 pF$ Type 1		100	400	ps
$t_{SK(PP)}$	Device to Device Skew similar path and conditions (See Figure 12) $C_L = 5 pF$			1	ns
$t_{JIT(PER)}$	Period Jitter RMS, 100 MHz (Source: $V_{ID} = 200 mV_{pp}$, $V_{CM} = 1 V$, tr/tf 0.5 ns, 10 and 90 % points, 30k samples. Source jitter de-embedded from Output values) (See Figure 14)		4	8	ps
$t_{JIT(PP)}$	Peak-to-peak Jitter, 200 Mbps $2^{15}-1$ PRBS (Source tr/tf 0.5 ns, 10% and 90% points, 100k samples. Source jitter de-embedded from Output values) (See Figure 14) Type 1		300	800	ps
tr / tf	Differential Output rise and fall times (See Figure 14) $C_L = 15 pF$	1		2.3	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

7. Typ value at $25^\circ C$ and 3.3 VCC supply voltage. .

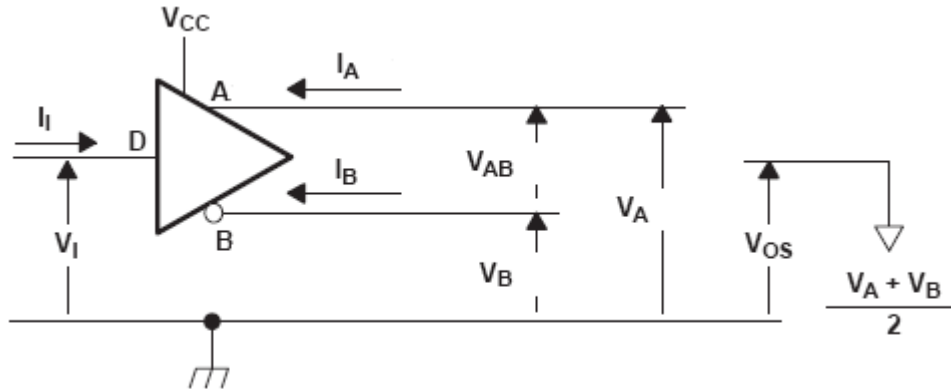
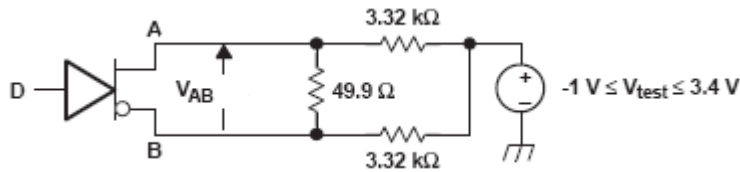
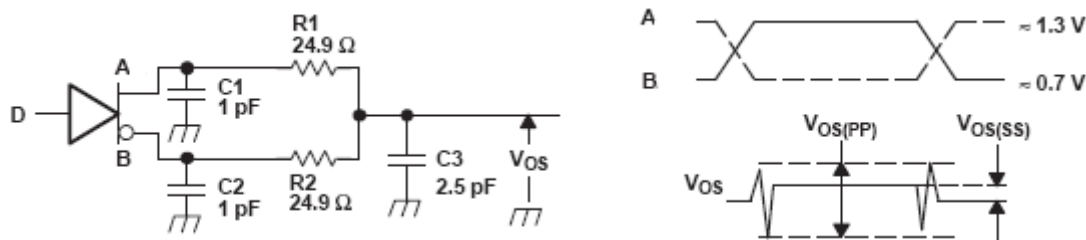


Figure 3. Driver Voltage and Current Definitions



A. All resistors are 1% tolerance.

Figure 4. Differential Output Voltage Test Circuit



- A. All input pulses are supplied by a generator having the following characteristics: t_r or $t_f \leq 1$ ns, pulse frequency = 500 kHz, duty cycle = $50 \pm 5\%$.
 B. C1, C2 and C3 include instrumentation and fixture capacitance within 2 cm of the D.U.T. and are 20% tolerance.
 C. R1 and R2 are metal film, surface mount, 1% tolerance, and located within 2 cm of the D.U.T.
 D. The measurement of $V_{OS(PP)}$ is made on test equipment with a -3 dB bandwidth of at least 1 GHz.

Figure 5. Test Circuit and Definitions for the Driver Common-Mode Output Voltage

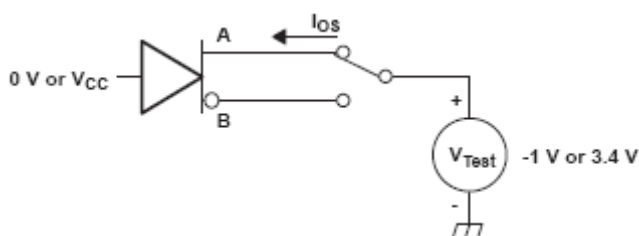
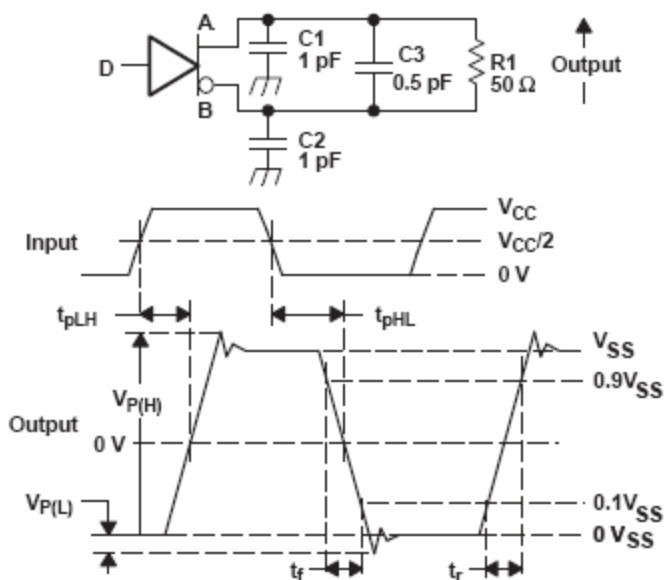


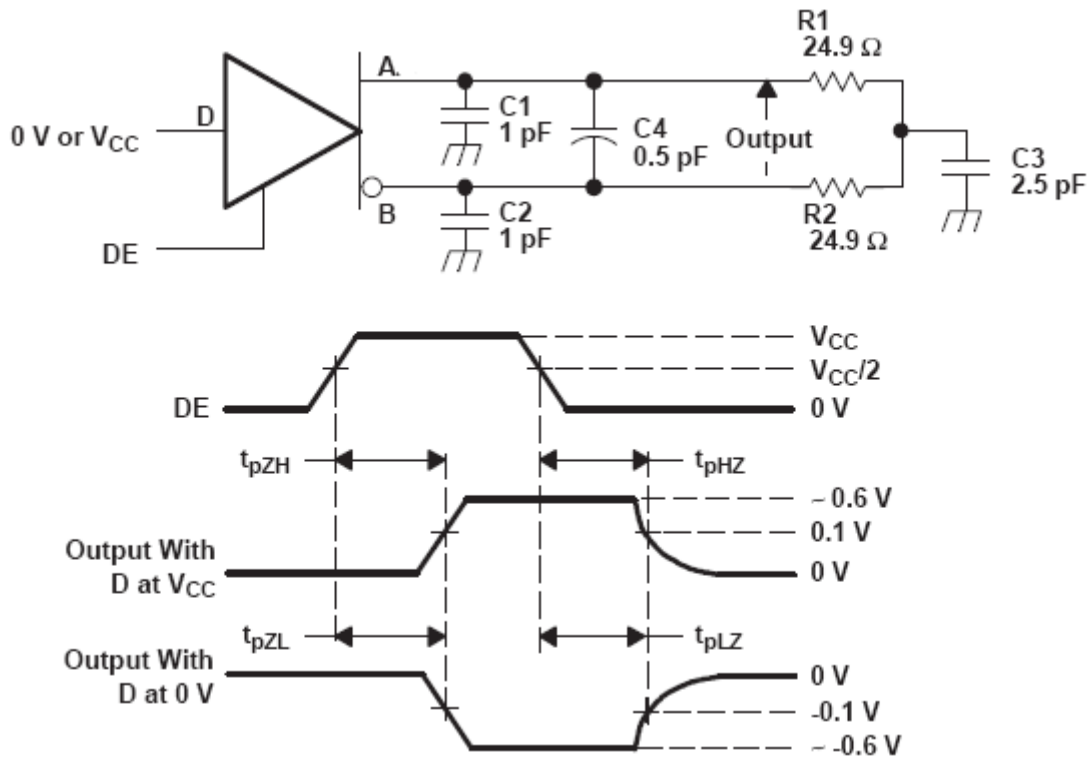
Figure 6. Driver Short-Circuit Test Circuit



- A. All input pulses are supplied by a generator having the following characteristics: t_r or $t_f \leq 1$ ns, frequency = 500 kHz, duty cycle = $50 \pm 5\%$.
 B. C1, C2, and C3 include instrumentation and fixture capacitance within 2 cm of the D.U.T. and are 20%.
 C. R1 is a metal film, surface mount, and 1% tolerance and located within 2 cm of the D.U.T.
 D. The measurement is made on test equipment with a -3 dB bandwidth of at least 1 GHz.

Figure 7. Driver Test Circuit, Timing, and Voltage Definitions for the Differential Output Signal

NBA3N200S



- A. All input pulses are supplied by a generator having the following characteristics: t_r or $t_f \leq 1$ ns, frequency = 500 kHz, duty cycle = $50 \pm 5\%$.
- B. C1, C2, C3, and C4 includes instrumentation and fixture capacitance within 2 cm of the D.U.T. and are 20%.
- C. R1 and R2 are metal film, surface mount, and 1% tolerance and located within 2 cm of the D.U.T.
- D. The measurement is made on test equipment with a -3 dB bandwidth of at least 1 GHz.

Figure 8. Driver Enable and Disable Time Circuit and Definitions

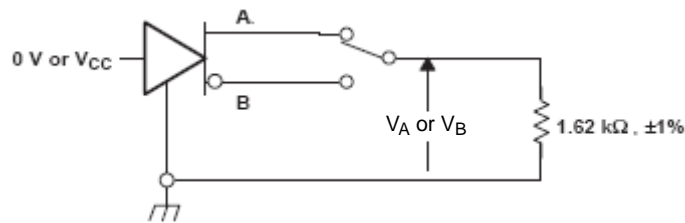
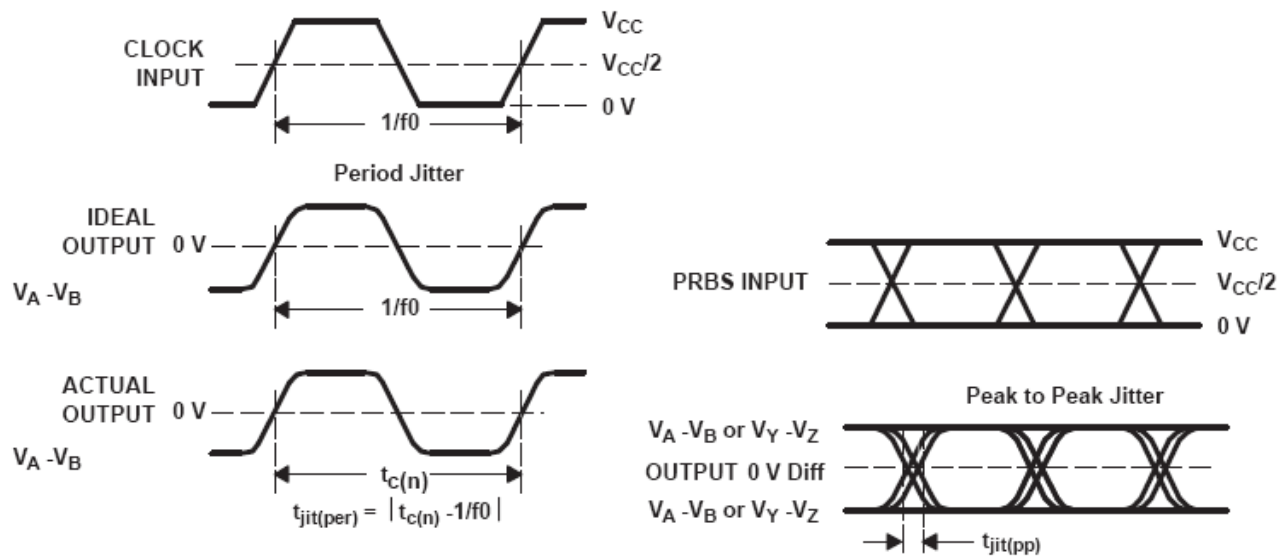


Figure 9. Maximum Steady State Output Voltage



- A. All input pulses are supplied by an Agilent 8304A Stimulus System.
 B. The measurement is made on a TEK TDS6604 running TDSJIT3 application software
 C. Period jitter is measured using a 100 MHz 50 \pm 1% duty cycle clock input.
 D. Peak-to-peak jitter is measured using a 200 Mbps 2₁₅-1 PRBS input.

Figure 10. Driver Jitter Measurement Waveforms

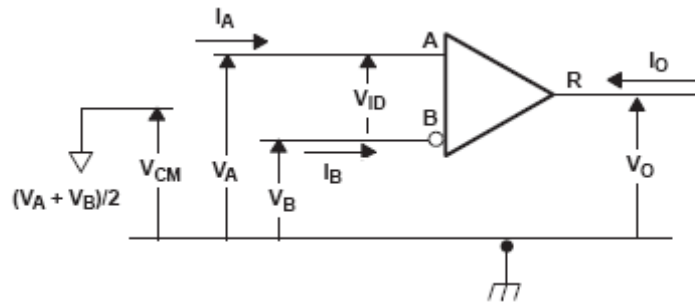
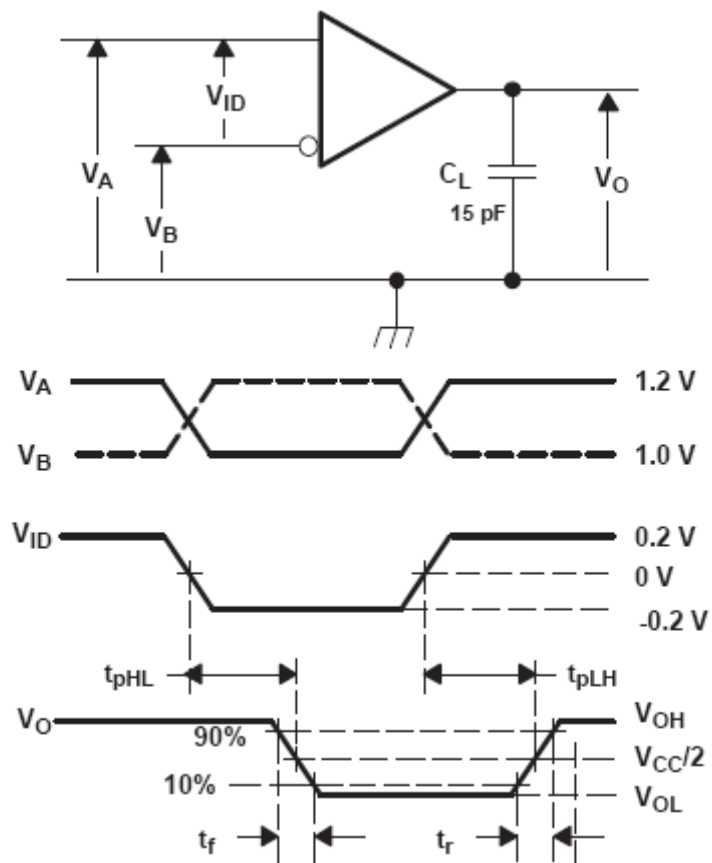


Figure 11. Receiver Voltage and Current Definitions

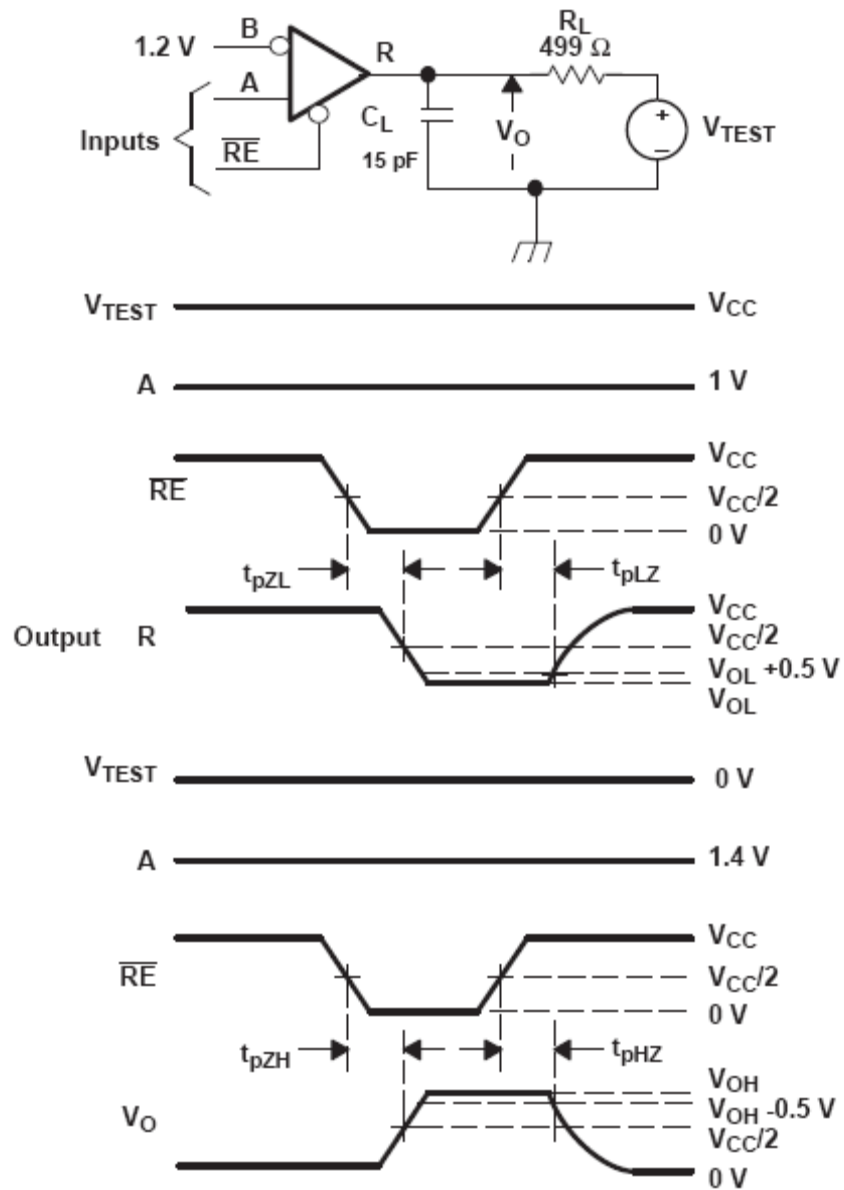
NBA3N200S



- A. All input pulses are supplied by a generator having the following characteristics: t_r or $t_f \leq 1 \text{ ns}$, frequency = 50 MHz, duty cycle = 50 $\pm 5\%$. C_L is a combination of a 20%–tolerance, low–loss ceramic, surface–mount capacitor and fixture capacitance within 2 cm of the D.U.T.
- B. The measurement is made on test equipment with a –3 dB bandwidth of at least 1 GHz.

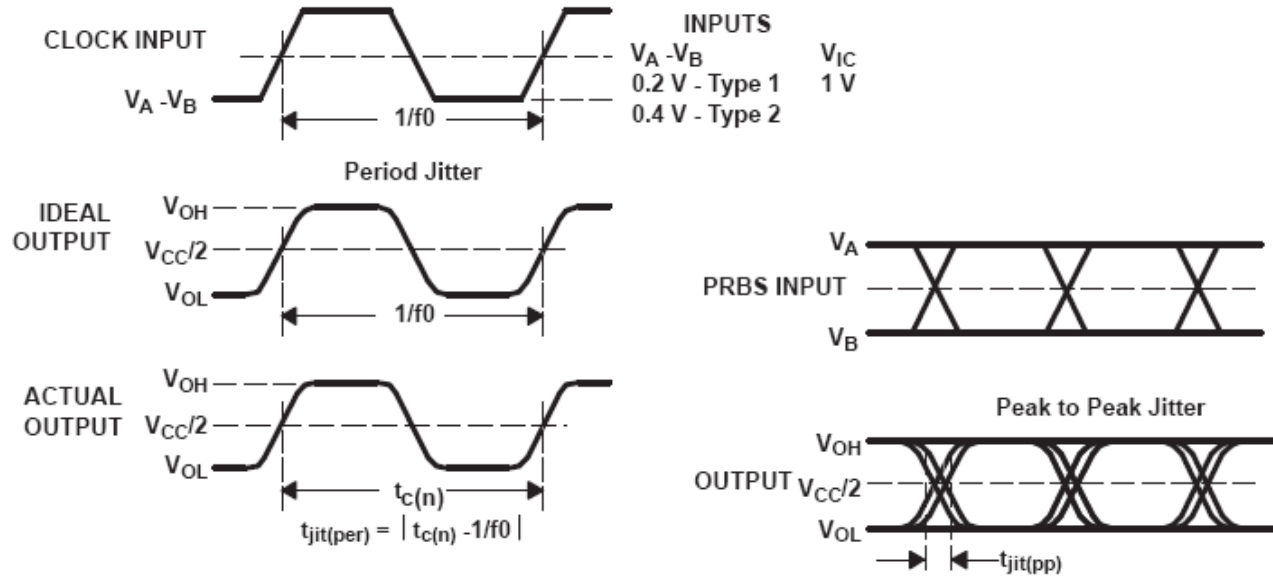
Figure 12. Receiver Timing Test Circuit and Waveforms

NBA3N200S



- A. All input pulses are supplied by a generator having the following characteristics: t_r or $t_f \leq 1$ ns, frequency = 500 kHz, duty cycle = 50 \pm 5%.
- B. R_L is 1% tolerance, metal film, surface mount, and located within 2 cm of the D.U.T.
- C. C_L is the instrumentation and fixture capacitance within 2 cm of the DUT and 20%.

Figure 13. Receiver Enable/Disable Time Test Circuit and Waveforms



- A. All input pulses are supplied by an Agilent 8304A Stimulus System.
 B. The measurement is made on a TEK TDS6604 running TDSJIT3 application software
 C. Period jitter is measured using a 100 MHz 50 \pm 1% duty cycle clock input.
 D. Peak-to-peak jitter is measured using a 200 Mbps $2^{15}-1$ PRBS input.

Figure 14. Receiver Jitter Measurement Waveforms

Table 8. TYPE-1 RECEIVER INPUT THRESHOLD TEST VOLTAGES

Applied Voltages		Resulting Differential Input Voltage	Resulting Common-Mode Input Voltage	Receiver Output
VIA	VIB	VID	VIC	
2.400	0.000	2.400	1.200	H
0.000	2.400	-2.400	1.200	L
3.800	3.750	0.050	3.775	H
3.750	3.800	-0.050	3.775	L
-1.350	-1.400	0.050	-1.375	H
-1.400	-1.350	-0.050	-1.375	L

H = high level, L = low level, output state assumes receiver is enabled ($\overline{RE} = L$)

NBA3N200S

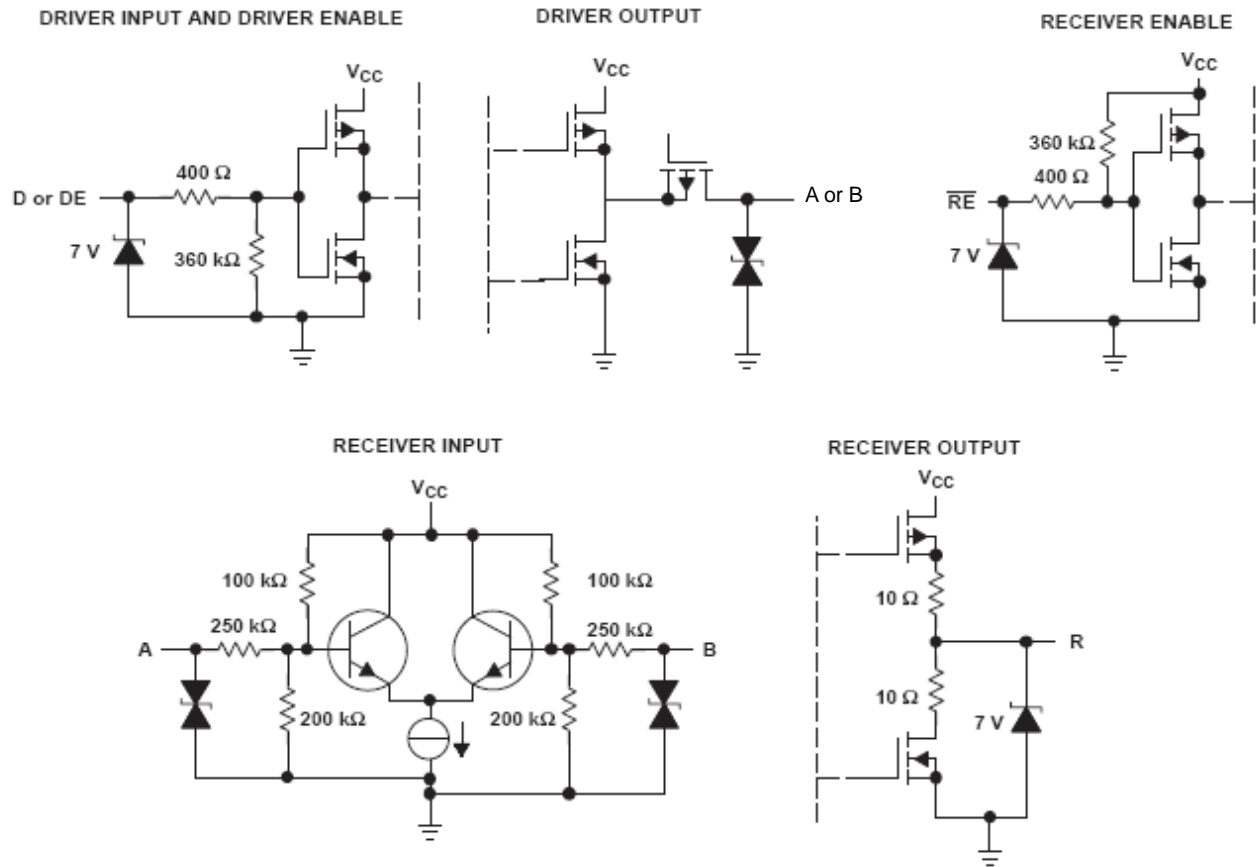


Figure 15. Equivalent Input and Output Schematic Diagrams

APPLICATION INFORMATION

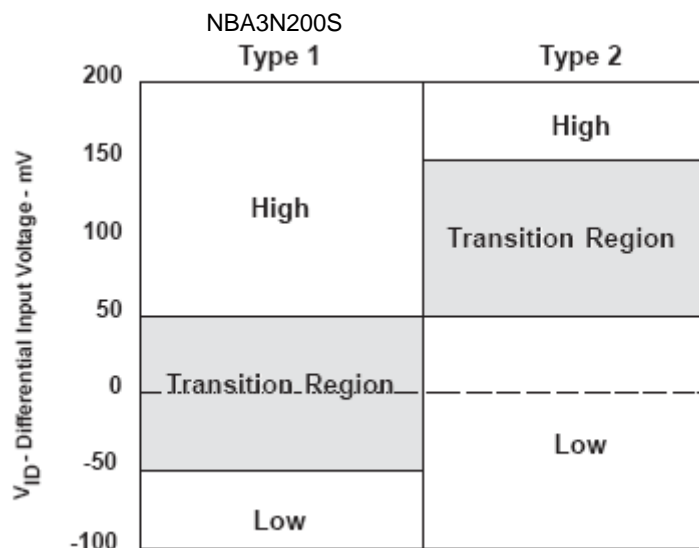
Receiver Input Threshold (Failsafe)

The MLVDS standard defines a type 1 and type 2 receiver. Type 1 receivers include no provisions for failsafe and have their differential input voltage thresholds near zero volts.

Type 2 receivers have their differential input voltage thresholds offset from zero volts to detect the absence of a voltage difference. The impact to receiver output by the offset input can be seen in Table 9 and Figure 16.

Table 9. RECEIVER INPUT VOLTAGE THRESHOLD REQUIREMENTS

Receiver Type	Output Low	Output High
Type 1	$-2.4\text{ V} \leq \text{VID} \leq -0.05\text{ V}$	$0.05\text{ V} \leq \text{VID} \leq 2.4\text{ V}$
Type 2	$-2.4\text{ V} \leq \text{VID} \leq 0.05\text{ V}$	$0.15\text{ V} \leq \text{VID} \leq 2.4\text{ V}$

**Figure 16. Receiver Differential Input Voltage Showing Transition Regions by Type****LIVE INSERTION/GLITCH-FREE POWER UP/DOWN**

The NBA3N200S provides a glitch-free power up/down feature that prevents the M-LVDS outputs of the device from turning on during a power up or power down event. This is especially important in live insertion applications, when a device is physically connected to an M-LVDS multipoint bus and V_{CC} is ramping.

While the M-LVDS interface for these devices is glitch free on power up/down, the receiver output structure is not.

Figure 17 shows the performance of the receiver output pin, R (CHANNEL 2), as V_{CC} (CHANNEL 1) is ramped. The glitch on the R pin is independent of the RE voltage. Any complications or issues from this glitch are easily resolved in power sequencing or system requirements that suspend operation until V_{CC} has reached a steady state value.

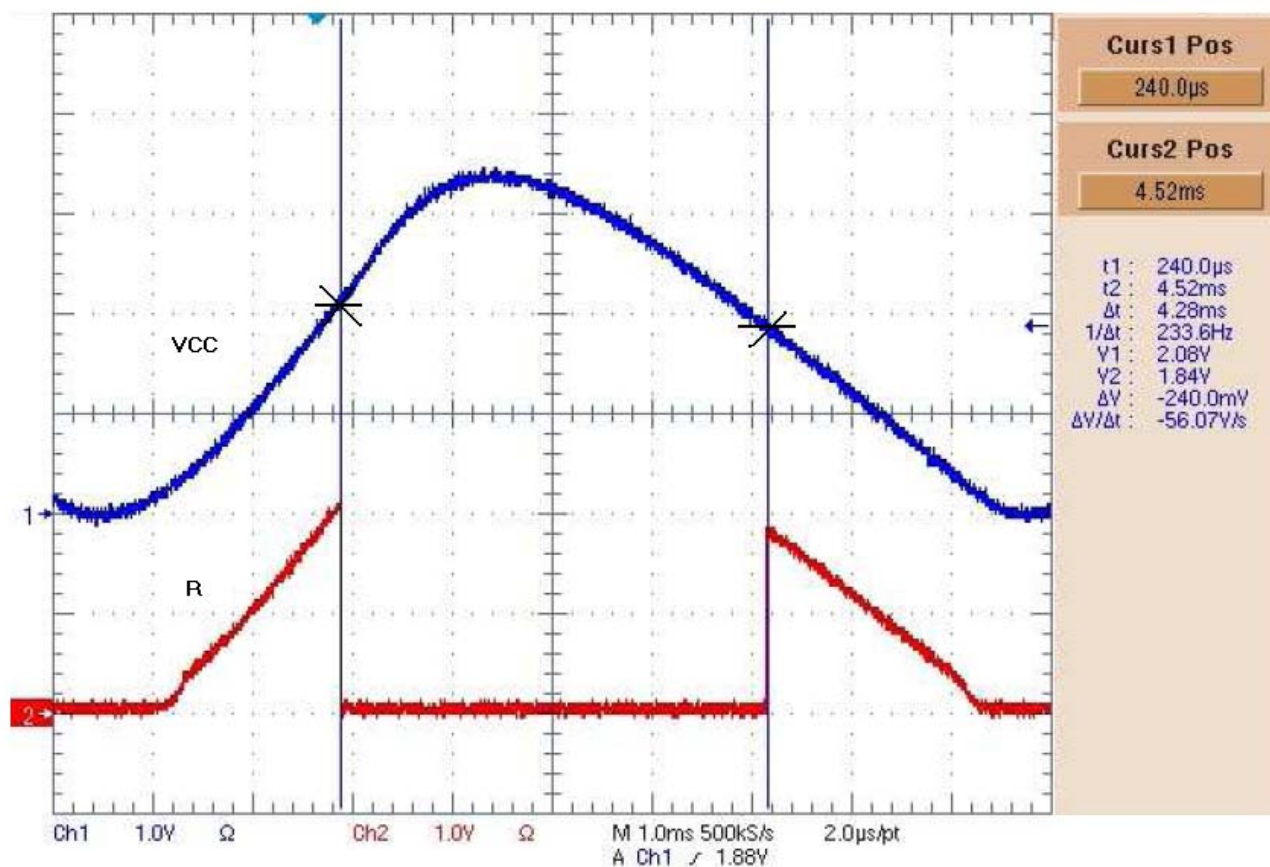


Figure 17. M-LVDS Receiver Output: VCC (CHANNEL 1), R Pin (CHANNEL 2)

Simplex Theory Configurations: Data flow is unidirectional and Point-to-Point from one Driver to one Receiver. NBA3N200S devices provide a high signal current allowing long drive runs and high noise immunity. Single terminated interconnects yield high amplitude levels.

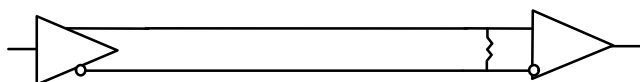


Figure 18. Point-to-Point Simplex Single Termination

Parallel terminated interconnects yield typical MLVDS amplitude levels and minimizes reflections. See Figures 18 and 19. A NBA3N200S can be used as the driver or as a receiver.

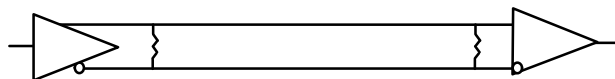


Figure 19. Parallel-Terminated Simplex

Simplex Multidrop Theory Configurations: Data flow is unidirectional from one Driver with one or more Receivers. Multiple boards required. Single terminated interconnects yield high amplitude levels. Parallel terminated interconnects yield typical MLVDS amplitude levels and

minimizes reflections. On the Evaluation Test Board, Headers P1, P2, and P3 may be used as need to interconnect transceivers to a each other or a bus. See Figures 20 and 21. A NBA3N200S can be used as the driver or as a receiver.

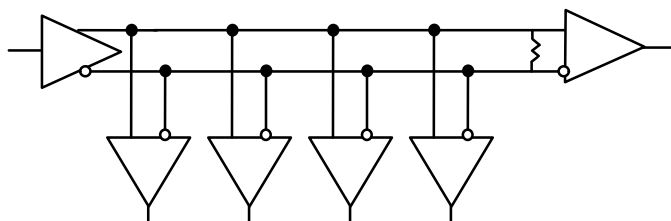


Figure 20. Multidrop or Distributed Simplex with Single Termination

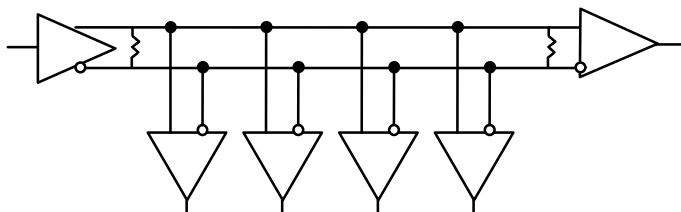


Figure 21. Multidrop or Distributed Simplex with Double Termination

Half Duplex Multinode Multipoint Theory Configurations: Data flow is unidirectional and selected from one of multiple possible Drivers to multiple Receivers. One “Two Node” multipoint connection can be accomplished with a single evaluation test board. More than Two Nodes requires multiple evaluation test boards. Parallel terminated interconnects yield typical MLVDS amplitude

levels and minimizes reflections. Parallel terminated interconnects yield typical LMVDS amplitude levels and minimizes reflections. On the Test Board, Headers P1, P2, and P3 may be used as need to interconnect transceivers to each other or a bus. See Figure 22. A NBA3N200S can be used as the driver or as a receiver.

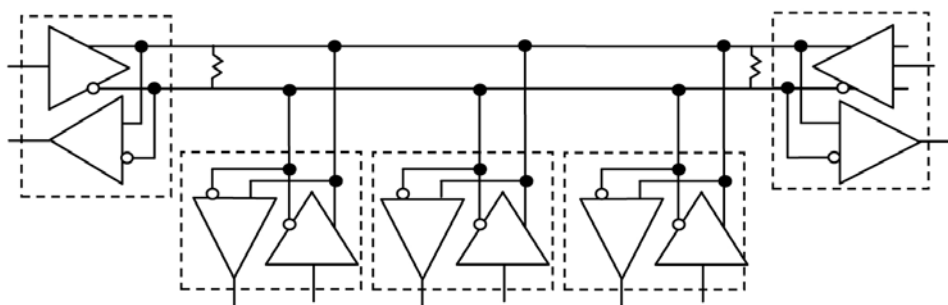


Figure 22. Multinode Multipoint Half Duplex (requires Double Termination)

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

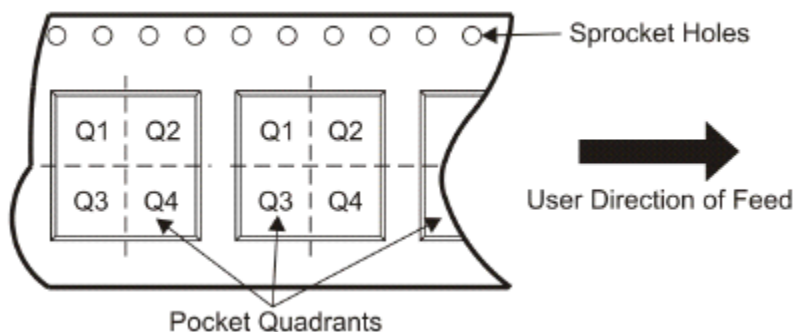


Figure 23.

NBA3N200S

ORDERING INFORMATION

Device	Receiver	Pin 1 Quadrant	Package	Shipping†
NBA3N200SDG	Type 1	Q1	SOIC – 8 (Pb–Free)	98 Units / Rail
NBA3N200SDR2G	Type 1	Q1	SOIC – 8 (Pb–Free)	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

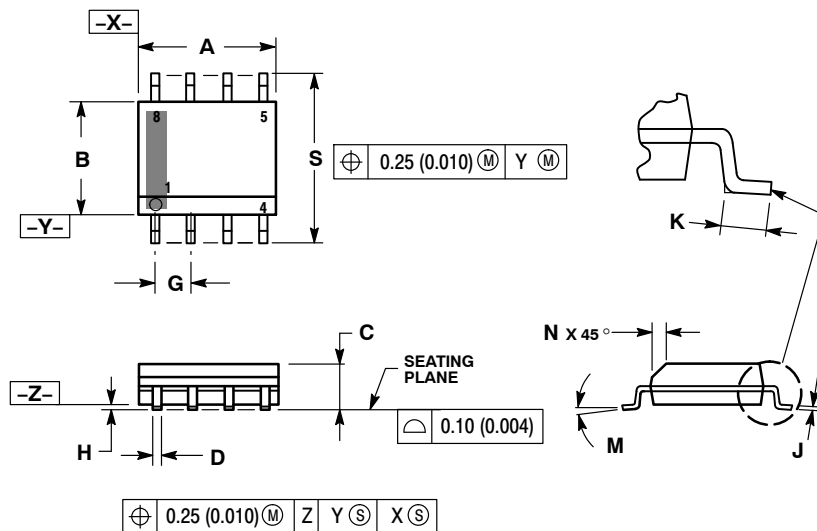
ON Semiconductor®



SCALE 1:1

SOIC-8 NB
CASE 751-07
ISSUE AK

DATE 16 FEB 2011



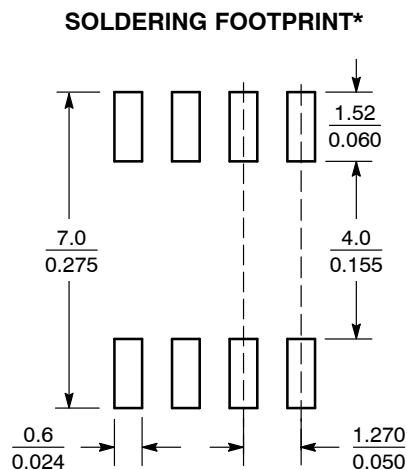
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

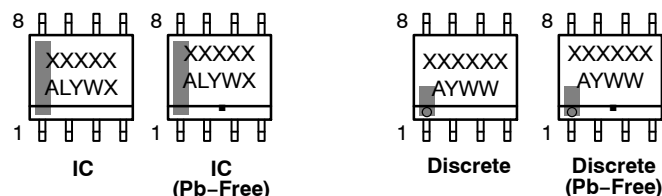
DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.197
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
H	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0°	8°	0°	8°
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

GENERIC

MARKING DIAGRAM*



SCALE 6:1 (mm/inches)



XXXXXX = Specific Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb-Free Package

XXXXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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SOIC-8 NB
CASE 751-07
ISSUE AK

DATE 16 FEB 2011

STYLE 1: PIN 1. EMITTER 2. COLLECTOR 3. COLLECTOR 4. EMITTER 5. EMITTER 6. BASE 7. BASE 8. EMITTER	STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 3. COLLECTOR, #2 4. COLLECTOR, #2 5. BASE, #2 6. EMITTER, #2 7. BASE, #1 8. EMITTER, #1	STYLE 3: PIN 1. DRAIN, DIE #1 2. DRAIN, #1 3. DRAIN, #2 4. DRAIN, #2 5. GATE, #2 6. SOURCE, #2 7. GATE, #1 8. SOURCE, #1	STYLE 4: PIN 1. ANODE 2. ANODE 3. ANODE 4. ANODE 5. ANODE 6. ANODE 7. ANODE 8. COMMON CATHODE
STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN 4. DRAIN 5. GATE 6. GATE 7. SOURCE 8. SOURCE	STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN 4. SOURCE 5. SOURCE 6. GATE 7. GATE 8. SOURCE	STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS 3. THIRD STAGE SOURCE 4. GROUND 5. DRAIN 6. GATE 3 7. SECOND STAGE Vd 8. FIRST STAGE Vd	STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 3. BASE, #2 4. COLLECTOR, #2 5. COLLECTOR, #2 6. EMITTER, #2 7. EMITTER, #1 8. COLLECTOR, #1
STYLE 9: PIN 1. EMITTER, COMMON 2. COLLECTOR, DIE #1 3. COLLECTOR, DIE #2 4. EMITTER, COMMON 5. EMITTER, COMMON 6. BASE, DIE #2 7. BASE, DIE #1 8. EMITTER, COMMON	STYLE 10: PIN 1. GROUND 2. BIAS 1 3. OUTPUT 4. GROUND 5. GROUND 6. BIAS 2 7. INPUT 8. GROUND	STYLE 11: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. DRAIN 2 7. DRAIN 1 8. DRAIN 1	STYLE 12: PIN 1. SOURCE 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 13: PIN 1. N.C. 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN	STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE 4. P-GATE 5. P-DRAIN 6. P-DRAIN 7. N-DRAIN 8. N-DRAIN	STYLE 15: PIN 1. ANODE 1 2. ANODE 1 3. ANODE 1 4. ANODE 1 5. CATHODE, COMMON 6. CATHODE, COMMON 7. CATHODE, COMMON 8. CATHODE, COMMON	STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #2 4. BASE, DIE #2 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 7. COLLECTOR, DIE #1 8. COLLECTOR, DIE #1
STYLE 17: PIN 1. VCC 2. V2OUT 3. V1OUT 4. TXE 5. RXE 6. VEE 7. GND 8. ACC	STYLE 18: PIN 1. ANODE 2. ANODE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. CATHODE 8. CATHODE	STYLE 19: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. MIRROR 1	STYLE 20: PIN 1. SOURCE (N) 2. GATE (N) 3. SOURCE (P) 4. GATE (P) 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3. CATHODE 3 4. CATHODE 4 5. CATHODE 5 6. COMMON ANODE 7. COMMON ANODE 8. CATHODE 6	STYLE 22: PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3. COMMON CATHODE/VCC 4. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND	STYLE 23: PIN 1. LINE 1 IN 2. COMMON ANODE/GND 3. COMMON ANODE/GND 4. LINE 2 IN 5. LINE 2 OUT 6. COMMON ANODE/GND 7. COMMON ANODE/GND 8. LINE 1 OUT	STYLE 24: PIN 1. BASE 2. EMITTER 3. COLLECTOR/ANODE 4. COLLECTOR/ANODE 5. CATHODE 6. CATHODE 7. COLLECTOR/ANODE 8. COLLECTOR/ANODE
STYLE 25: PIN 1. VIN 2. N/C 3. REXT 4. GND 5. IOUT 6. IOUT 7. IOUT 8. IOUT	STYLE 26: PIN 1. GND 2. dv/dt 3. ENABLE 4. ILIMIT 5. SOURCE 6. SOURCE 7. SOURCE 8. VCC	STYLE 27: PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ 5. SOURCE 6. SOURCE 7. SOURCE 8. DRAIN	STYLE 28: PIN 1. SW_TO_GND 2. DASIC_OFF 3. DASIC_SW_DET 4. GND 5. V_MON 6. VBULK 7. VBULK 8. VIN
STYLE 29: PIN 1. BASE, DIE #1 2. EMITTER, #1 3. BASE, #2 4. EMITTER, #2 5. COLLECTOR, #2 6. COLLECTOR, #2 7. COLLECTOR, #1 8. COLLECTOR, #1	STYLE 30: PIN 1. DRAIN 1 2. DRAIN 1 3. GATE 2 4. SOURCE 2 5. SOURCE 1/DRAIN 2 6. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2 8. GATE 1		

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